MJ15001 (NPN), MJ15002 (PNP)

Complementary Silicon Power Transistors

The MJ15001 and MJ15002 are EpiBase[™] power transistors designed for high power audio, disk head positioners and other linear applications.

Features

- High Safe Operating Area (100% Tested) 5.0 A @ 40 V
 0.5 A @ 100 V
- For Low Distortion Complementary Designs
- High DC Current Gain $-h_{FE} = 25$ (Min) @ $I_C = 4$ Adc
- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	140	Vdc
Collector-Base Voltage	V _{CBO}	140	Vdc
Emitter-Base Voltage	V _{EBO}	5	Vdc
Collector Current – Continuous	Ic	15	Adc
Base Current – Continuous	I _B	5	Adc
Emitter Current – Continuous	ΙE	20	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	200 1.14	W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	0.875	°C/W
Maximum Lead Temperature for Soldering Purposes 1/16" from Case for ≤ 10 secs	TL	265	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



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20 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 140 VOLTS, 250 WATTS



TO-204AA (TO-3) CASE 1-07 STYLE 1

MARKING DIAGRAM



MJ1500x = Device Code

x = 1 or 2

G = Pb-Free Package

A = Location Code YY = Year

WW = Work Week

MEX = Country of Orgin

ORDERING INFORMATION

Device	Package	Shipping
MJ15001	TO-204AA	100 Units/Tray
MJ15001G	TO-204AA (Pb-Free)	100 Units/Tray
MJ15002	TO-204AA	100 Units/Tray
MJ15002G	TO-204AA (Pb-Free)	100 Units/Tray

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	-	1	II.	· I
Collector–Emitter Sustaining Voltage (Note 1) $(I_C, = 200 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	140	-	Vdc
Collector Cutoff Current $(V_{CE} = 140 \text{ Vdc}, V_{BE(off)} = 1.5 \text{ Vdc})$ $(V_{CE} = 140 \text{ Vdc}, V_{BE(off)} = 1.5 \text{ Vdc}, T_{C} = 150^{\circ}\text{C})$	ICEX	_ _	100 2.0	μAdc mAdc
Collector Cutoff Current (V _{CE} = 140 Vdc, I _B = 0)	I _{CEO}	-	250	μAdc
Emitter Cutoff Current (V _{EB} = 5 Vdc, I _C = 0)	I _{EBO}	-	100	μAdc
SECOND BREAKDOWN				
Second Breakdown Collector Current with Base Forward Biased (V _{CE} = 40 Vdc, t = 1 s (non–repetitive)) (V _{CE} = 100 Vdc, t = 1 s (non–repetitive))	I _{S/b}	5.0 0.5	_ _	Adc
ON CHARACTERISTICS	,			•
DC Current Gain (I _C = 4 Adc, V _{CE} = 2 Vdc)	h _{FE}	25	150	-
Collector–Emitter Saturation Voltage (I _C = 4 Adc, I _B = 0.4 Adc)	V _{CE(sat)}	-	1.0	Vdc
Base–Emitter On Voltage (I _C = 4 Adc, V _{CE} = 2 Vdc)	V _{BE(on)}	-	2.0	Vdc
DYNAMIC CHARACTERISTICS	·			
Current–Gain — Bandwidth Product ($I_C = 0.5$ Adc, $V_{CE} = 10$ Vdc, $f_{test} = 0.5$ MHz)	f _T	2.0	-	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f _{test} = 1 MHz)	C _{ob}	-	1000	pF

^{1.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2%.

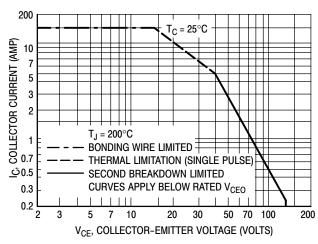


Figure 1. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on $T_{J (pk)} = 200^{\circ}C$; T_{C} is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

MJ15001 (NPN), MJ15002 (PNP)

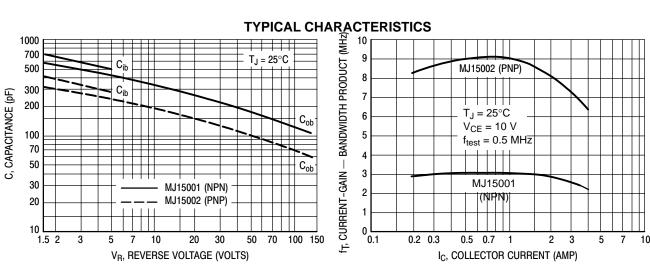


Figure 2. Capacitances

Figure 3. Current-Gain — Bandwidth Product

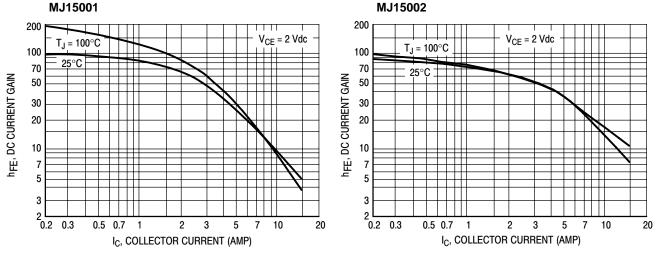


Figure 4. DC Current Gain

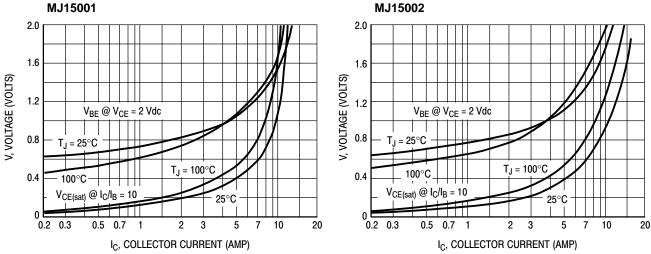
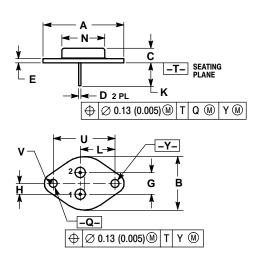


Figure 5. "On" Voltages

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PACKAGE DIMENSIONS

TO-204 (TO-3) CASE 1-07 ISSUE Z



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 V14 5M 1982
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- 3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INC	CHES MILLIMETERS		
DIM	MIN	MAX	MIN	MAX
Α	1.550 REF		39.37	'REF
В		1.050		26.67
С	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
Е	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
Н	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N		0.830		21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
٧	0.131	0.188	3.33	4.77

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

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